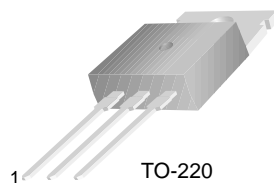


BD243/A/B/C

Medium Power Linear and Switching Applications

- Complement to BD244, BD244A, BD244B and BD244C respectively



1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage		
	: BD243	45	V
	: BD243A	60	V
	: BD243B	80	V
	: BD243C	100	V
V_{CEO}	Collector-Emitter Voltage		
	: BD243	45	V
	: BD243A	60	V
	: BD243B	80	V
	: BD243C	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current (DC)	6	A
I_{CP}	*Collector Current (Pulse)	10	A
I_B	Base Current	2	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	65	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{CEO(sus)}$	* Collector-Emitter Sustaining Voltage					
	: BD243	$I_C=30\text{mA}, I_B=0$	45			V
	: BD243A		60			V
	: BD243B		80			V
	: BD243C		100			V
I_{CEO}	Collector Cut-off Current	: BD243/243A $V_{CE} = 30\text{V}, I_B = 0$			0.7	mA
		: BD243B/243C $V_{CE} = 60\text{V}, I_B = 0$			0.7	mA
I_{CES}	Collector Cut-off Current	: BD243 $V_{CE} = 45\text{V}, V_{BE} = 0$			0.4	mA
		: BD243A $V_{CE} = 60\text{V}, V_{BE} = 0$			0.4	mA
		: BD243B $V_{CE} = 80\text{V}, V_{BE} = 0$			0.4	mA
		: BD243C $V_{CE} = 100\text{V}, V_{BE} = 0$			0.4	mA
		: BD243C $V_{CE} = 100\text{V}, V_{BE} = 0$			0.4	mA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$			1	mA
h_{FE}	*DC Current Gain	$V_{CE} = 4\text{V}, I_C = 0.3\text{A}$	30			
		$V_{CE} = 4\text{V}, I_C = 3\text{A}$	15			
$V_{CE(sat)}$	*Collector-Emitter Saturation Voltage	$I_C = 6\text{A}, I_B = 1\text{A}$			1.5	V
$V_{BE(on)}$	*Base-Emitter ON Voltage	$V_{CE} = 4\text{V}, I_C = 6\text{A}$			2	V

* Pulse Test :PW=300 μs , duty Cycle<20% Pulsed

Typical Characteristics

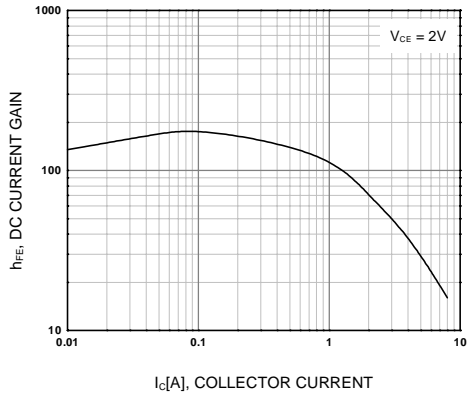


Figure 1. DC current Gain

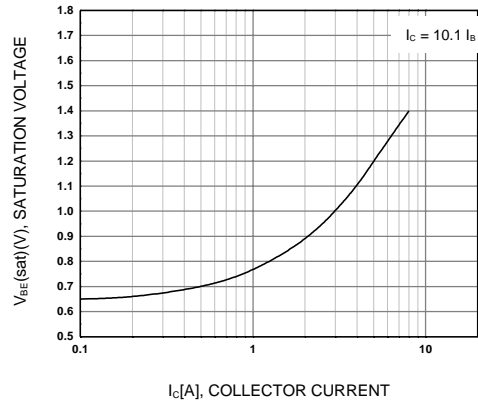


Figure 2. Base-Emitter Saturation Voltage

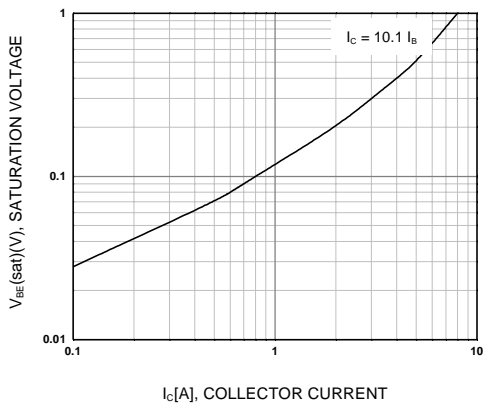


Figure 3. Collector-Emitter Saturation Voltage

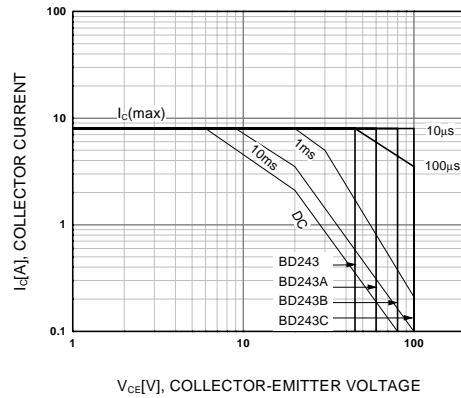


Figure 4. Safe Operating Area

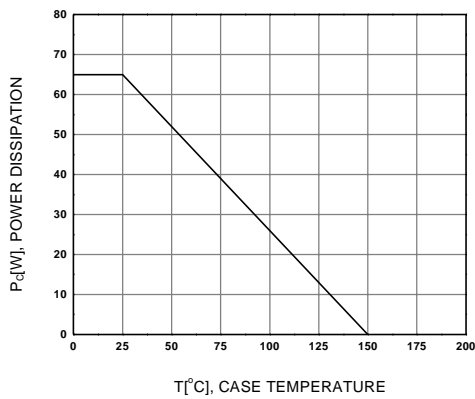


Figure 5. Power Derating

Package Dimensions

BD243/A/B/C

TO-220



Dimensions in Millimeters

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